## DESCRIPTION

The SP6007 is a low-drop diode emulator controller IC which when combined with an external MOS FET replaces Schottky diodes in high-efficiency flyback converters. The chip regulates the forward drop of an external MOS FET to about 40mV and switches it off as soon as the voltage becomes negative.

SP6007 is available in space saving SOT-23-6 package.

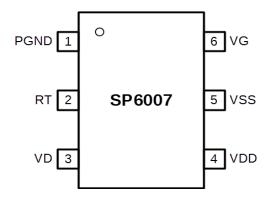
## **APPLICATIONS**

- Industrial Power Systems
- Distributed Power Systems
- Battery Powered Systems
- Flyback Converters

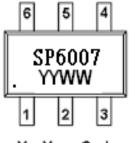
#### **FEATURES**

- Works with 5V Logic Level FETS Less Than 100mW Standby Power
- Fast Turn-off Delay of 25ns
- 3.6V~5.5V VDD operating range
- Supports DCM and Quasi-Resonant Operation
- Supports High-side and Low-side Rectification
- Available in space saving SOT-23-6 Package

## PIN CONFIGURATION (SOT-23-6L)

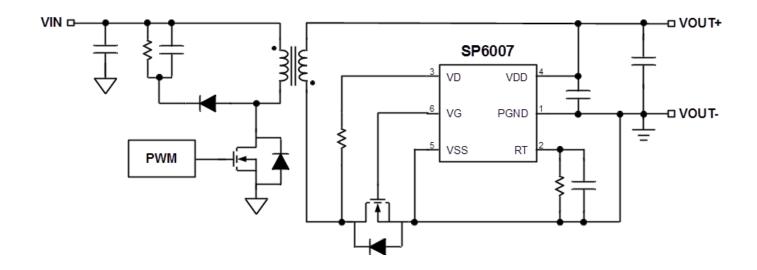


## **PART MARKING**



Y: Year Code W: Week Code

# TYPICAL APPLICATION CIRCUIT



## **PINDESCRIPTION**

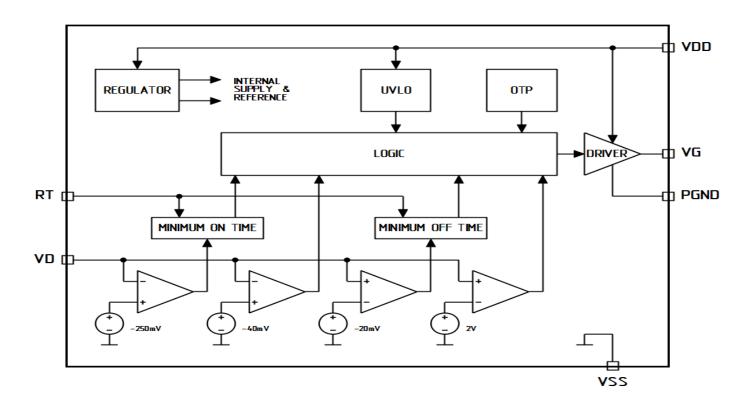
Pin No.	Pin Name	Description		
1	PGND	Power Ground, return for gate driver		
2	RT	Minimum On-time setting pin. A resistor connected between this pin and VSS		
		defines minimum On-time		
3	VD	External FET drain voltage sensing		
4	Vdd	DC supply voltage.		
5	VSS	Ground, also used as reference for VD		
6	VG	Gate driver output		

## **ORDERING INFORMATION**

Part Number	Package	Part Marking
SP6007S26RGB	SOT-23-6L	SP6007

※ SP6007S26RGB: Tape Reel; Pb − Free; Halogen − Free

## **BLOCK DIAGRAM**



# **ABSOLUTE MAXIMUM RATINGS** (TA=25°C, unless otherwise specified)

The following ratings designate persistent limits beyond which damage to the device may occur.

The following funds group persistent minus of one winter curring to the device may occur.					
Symbol	Parameter	Value	Unit		
Vdd	DC Supply Voltage	-0.3 ~ 7.0	V		
PGND	Power Ground, return for gate driver	-0.3 ~ 0.3	V		
VD	External FET drain voltage sensing	-1.0 ~ 60	V		
P <sub>D</sub>	Power Dissipation @ T <sub>A</sub> =85°C (*)	0.3	W		
$T_{J}$	Junction temperature	-40 ~ 150	°C		
T <sub>STG</sub>	Storage temperature	-40 ~ 150	°C		
T <sub>LEAD</sub>	Lead soldering temperature for 5 sec	260	°C		

## THERMAL RESISTANCE

Symbol	Parameter	Value	Unit
Rөja	Thermal Resistance Junction –to Ambient (*1)	220	°C/W
Rөjc	Thermal Resistance Junction –to Case (*2)	110	°C/W

<sup>(\*1)</sup>  $\theta$ JA is measured in natural convection (still air) at TA = 25°C with the component mounted on a low effective thermal conductivity test board of JEDEC 51-3 thermal measurement standard.

<sup>(\*2)</sup> The power dissipation and thermal resistance are evaluated under copper board mounted with free air conditions

# **ELECTRICAL CHARACTERISTICS**

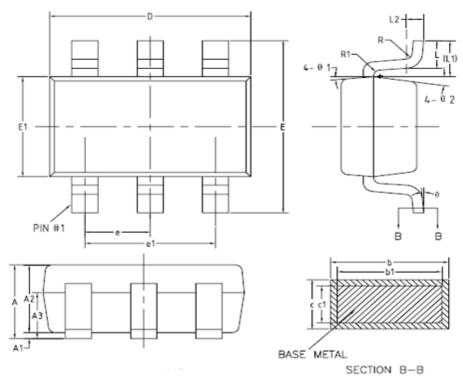
 $(T_A=25^{\circ}C, V_{DD}=5V, R_{RT}=100k\Omega, unless otherwise specified)$ 

Symbol	Parameter	Conditions	Min	Тур	Max	Unit	
Supply Section							
Vdd	Supply voltage		3.6		5.5	V	
Vdd on	Vdd UVLO rising				3.6	V	
Vdd	Vdd UVLO hysteresis		0.2			V	
hysteresis							
$I_{CC}$	Operating current	CLOAD=5nF, Fsw=100kHz			10	mA	
Iq	Quiescent current	$V_{SS}-V_D=0.5V$			3	mA	
	Shutdown current	V <sub>DD</sub> =3V			100	uA	
	Thermal shutdown			150		$^{\circ}$ C	
	Thermal shutdown hysteresis			30		$^{\circ}\mathrm{C}$	
Control Ci	rcuitry Section						
$V_{\rm fwd}$	VSS-VD forward voltage			40		mV	
	VSS-VD turn-off threshold			20		mV	
$T_{Don}$	Turn-on delay	C <sub>LOAD</sub> =5nF		100		nS	
		C <sub>LOAD</sub> =10nF		150		nS	
	Input bias current on VD pin	$V_D=60V$			1	uA	
T <sub>MIN</sub>	Minimum on-time	C <sub>LOAD</sub> =5nF		1.6		uS	
$V_{\mathrm{Boff}}$	Turn-off blanking V <sub>DS</sub>			2		V	
$V_{ON-DS}$	Turn-on V <sub>DS</sub> threshold			-250		mV	
Gate Drive	Gate Driver Section						
$V_{G-L}$	Gate output low voltage	I <sub>LOAD</sub> =1mA			0.1	V	
$V_{G-H}$	Gate output high voltage	V <sub>DD</sub> =5V	4.5			V	
	Turn-off propagation delay	$V_D=V_{SS}$		25		nS	
$T_{ m Doff}$	Turn-off total delay	V <sub>D</sub> =V <sub>SS</sub> , C <sub>LOAD</sub> =5nF,		35		nS	
		$R_{GATE}=0\Omega, V_{GS}=2V$					
		$\begin{array}{c} V_{D} = V_{SS}, C_{LOAD} = 10 nF, \\ R_{GATE} = 0\Omega, V_{GS} = 2V \end{array}$		45		nS	
	Maximum source current (*)			0.5		A	
	Maximum sink current (*)		2			A	
	Pull down impedance			1		Ω	

Notes:

(\*) Guaranteed by design and characterization

# SOT-23-6L PACKAGE OUTLINE



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SYMBOL	MIN	NOM	MAX
Α	1.05		1.30
A1	0.00		0.15
A2	0.90	1.10	1.30
A3	0.60	0.65	0.70
b	0.30		0.50
b1	0.32		0.45
С	0.10		0.25
c1	0.10		0.20
D	2.82	2.92	3.05
E	2.60	2.80	3.00
E1	1.50	1.60	1.75
e	0.95 REF		
e1	1.80	1.90	2.00
L	0.35 0.45 0.60		0.60
L1	0.59 REF		
L2	0.25BSC		
θ	0° 8°		
<i>θ</i> 1	3°	5°	7°
<b>θ</b> 2	6°	8*	10°

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